Electronic Supplementary Material (ESI) for RSC Advances.

Electronic supplementary information

The Effect of the Surface Energy and Structure of the SiC Substrate on Epitaxial Graphene Growth

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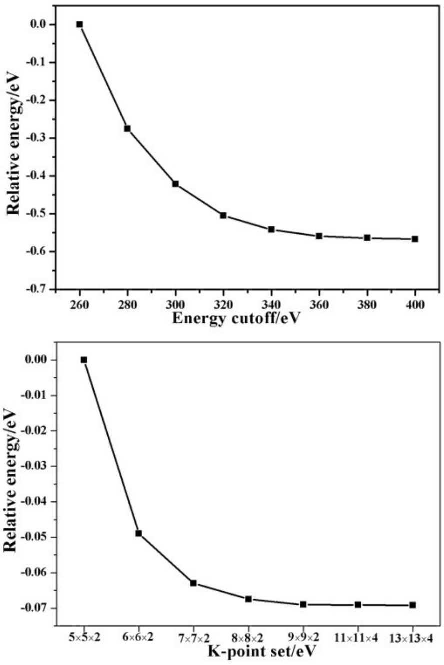
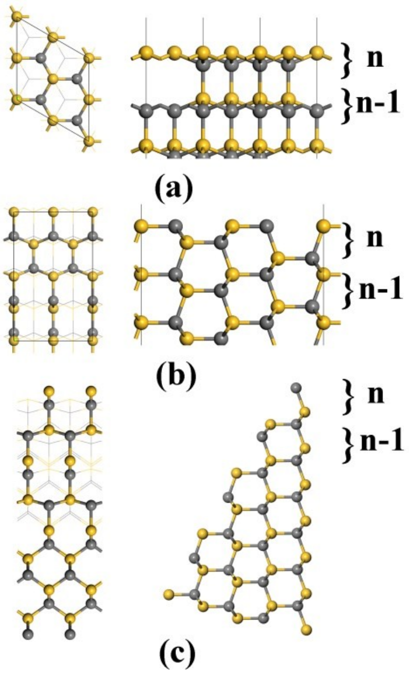
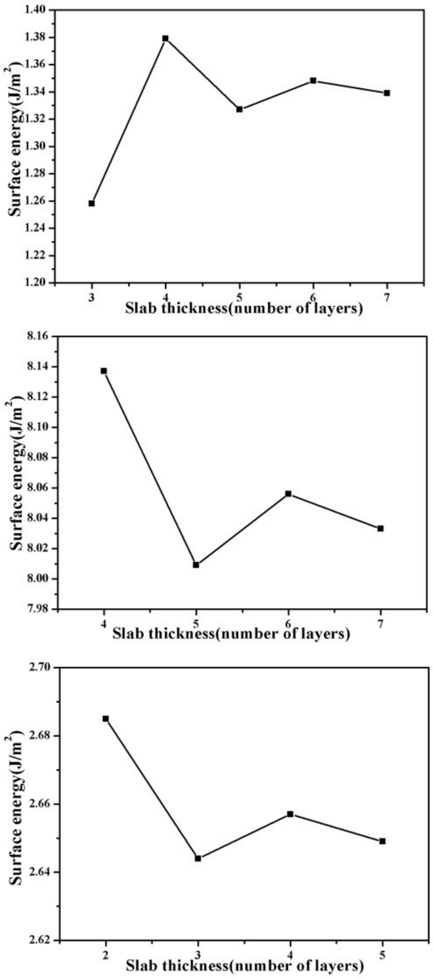


S 1. The convergence tests of energy cutoff and k-point.



S 2. The SiC surface models of (a) (0001), (b) (1000), and (c) (1-106) faces. The number of layers is labeled in the figure.



S 3. The surface energy influenced by the number of layers of the SiC surface models.